Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	84
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	3K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l071v8t6tr

Contents

2.2 Ultra-low-power device continuum

The ultra-low-power family offers a large choice of core and features, from 8-bit proprietary core up to ARM® Cortex®-M4, including ARM® Cortex®-M3 and ARM® Cortex®-M0+. The STM32Lx series are the best choice to answer your needs in terms of ultra-low-power features. The STM32 ultra-low-power series are the best solution for applications such as gaz/water meter, keyboard/mouse or fitness and healthcare application. Several built-in features like LCD drivers, dual-bank memory, low-power run mode, operational amplifiers, 128-bit AES, DAC, crystal-less USB and many other definitely help you building a highly cost optimized application by reducing BOM cost. STMicroelectronics, as a reliable and long-term manufacturer, ensures as much as possible pin-to-pin compatibility between all STM8Lx and STM32Lx on one hand, and between all STM32Lx and STM32Fx on the other hand. Thanks to this unprecedented scalability, your legacy application can be upgraded to respond to the latest market feature and efficiency requirements.

- **Stop mode without RTC**

  The Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are disabled.

  Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

  The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 3.5 µs, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on). It can also be wakened by the USART/I2C/LPUART/LPTIMER wakeup events.
- **Standby mode with RTC**

  The Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSE crystal and HSI RC oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

  The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.
- **Standby mode without RTC**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

  The device exits Standby mode in 60 µs when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

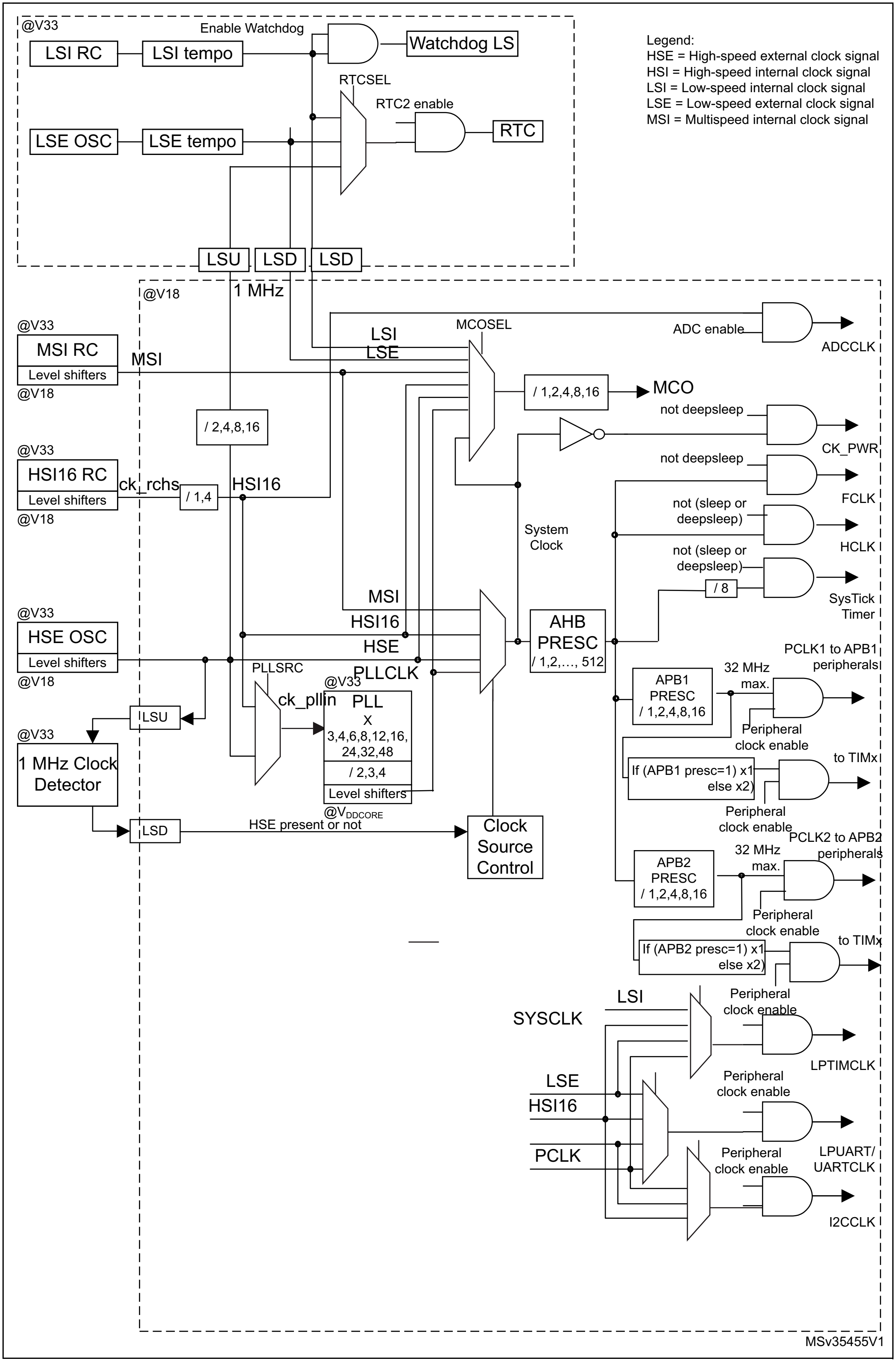
Table 3. Functionalities depending on the operating power supply range

Operating power supply range	Functionalities depending on the operating power supply range		
	ADC operation	Dynamic voltage scaling range	I/O operation
V_{DD} = 1.65 to 1.71 V	ADC only, conversion time up to 570 ksps	Range 2 or range 3	Degraded speed performance
V_{DD} = 1.71 to 1.8 V(1)	ADC only, conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Degraded speed performance
V_{DD} = 1.8 to 2.0 V(1)	Conversion time up to 1.14 Msps	Range1, range 2 or range 3	Degraded speed performance

Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued)(1)(2)

IPs	Run/Active	Sleep	Low-power run	Low-power sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
High Speed External (HSE)	O	O	O	O	--		--	
Low Speed Internal (LSI)	O	O	O	O	O		O	
Low Speed External (LSE)	O	O	O	O	O		O	
Multi-Speed Internal (MSI)	O	O	Y	Y	--		--	
Inter-Connect Controller	Y	Y	Y	Y	Y		--	
RTC	O	O	O	O	O	O	O	
RTC Tamper	O	O	O	O	O	O	O	O
Auto WakeUp (AWU)	O	O	O	O	O	O	O	O
USART	O	O	O	O	O(4)	O	--	
LPUART	O	O	O	O	O(4)	O	--	
SPI	O	O	O	O	--		--	
I2C	O	O	O	O	O(5)	O	--	
ADC	O	O	--	--	--		--	
Temperature sensor	O	O	O	O	O		--	
Comparators	O	O	O	O	O	O	--	
16-bit timers	O	O	O	O	--		--	
LPTIMER	O	O	O	O	O	O		
IWDG	O	O	O	O	O	O	O	O
WWDG	O	O	O	O	--		--	
SysTick Timer	O	O	O	O			--	
GPIOs	O	O	O	O	O	O		2 pins
Wakeup time to Run mode	0 µs	0.36 µs	3 µs	32 µs	3.5 µs		50 µs	

Figure 2. Clock tree



3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 29 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 84 GPIOs can be connected to the 16 configurable interrupt/event lines. The 13 other lines are connected to PVD, RTC, USARTs, I2C, LPUART, LPTIMER or comparator events.

Table 15. STM32L071xxx pin definition (continued)

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32[(1)]	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100						
-	-	-	11	-	-	18	K2	PC3	I/O	FT	-	LPTIM1_ETR, SPI2_MOSI/I2S2_SD	ADC_IN13
-	4	8	12	F1	-	19	J1	VSSA	S		-	-	-
-	-	-	-	-	-	20	K1	VREF-	S		-	-	-
-	-	-	-	G1	E6	21	L1	VREF+	S		-	-	-
5	5	9	13	H1	F7	22	M1	VDDA	S		-	-	-
6	6	10	14	G2	E5	23	L2	PA0	I/O	TTa	-	TIM2_CH1, USART2_CTS, TIM2_ETR, USART4_TX, COMP1_OUT	COMP1_INM, ADC_IN0, RTC_TAMP2/WKUP1
7	7	11	15	H2	E4	24	M2	PA1	I/O	FT	-	EVENTOUT, TIM2_CH2, USART2_RTS_DE, TIM21_ETR, USART4_RX	COMP1_INP, ADC_IN1
8	8	12	16	F3	F6	25	K3	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, USART2_TX, LPUART1_TX, COMP2_OUT	COMP2_INM, ADC_IN2
9	9	13	17	G3	G7	26	L3	PA3	I/O	FT	-	TIM21_CH2, TIM2_CH4, USART2_RX, LPUART1_RX	COMP2_INP, ADC_IN3
-	-	-	18	C2	-	27	D3	VSS	S	-	-	-	-
-	-	-	19	D2	-	28	H3	VDD	S	-	-	-	-
10	10	14	20	H3	F5	29	M3	PA4	I/O	TC	-	SPI1_NSS, USART2_CK, TIM22_ETR	COMP1_INM, COMP2_INM, ADC_IN4
11	11	15	21	F4	G6	30	K4	PA5	I/O	TC	-	SPI1_SCK, TIM2_ETR, TIM2_CH1	COMP1_INM, COMP2_INM, ADC_IN5

Table 15. STM32L071xxx pin definition (continued)

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32[(1)]	LQFP48	LQFP64	UFBGA64	WLCSP49	LQFP100	UFBG100						
12	12	16	22	G4	G5	31	L4	PA6	I/O	FT	-	SPI1_MISO, TIM3_CH1, LPUART1_CTS, TIM22_CH1, EVENTOUT, COMP1_OUT	ADC_IN6
13	13	17	23	H4	F4	32	M4	PA7	I/O	FT	-	SPI1_MOSI, TIM3_CH2, TIM22_CH2, EVENTOUT, COMP2_OUT	ADC_IN7
-	-	-	24	H5	-	33	K5	PC4	I/O	FT	-	EVENTOUT, LPUART1_TX	ADC_IN14
-	-	-	25	H6	-	34	L5	PC5	I/O	FT	-	LPUART1_RX	ADC_IN15
14	14	18	26	F5	G4	35	M5	PB0	I/O	FT	-	EVENTOUT, TIM3_CH3	ADC_IN8, VREF_OUT
15	15	19	27	G5	D3	36	M6	PB1	I/O	FT	-	TIM3_CH4, LPUART1_RTS_DE	ADC_IN9, VREF_OUT
-	-	20	28	G6	E3	37	L6	PB2	I/O	FT	-	LPTIM1_OUT, I2C3_SMBA	-
-	-	-	-	-	-	38	M7	PE7	I/O	FT	-	USART5_CK/USART5_RTS_DE	-
-	-	-	-	-	-	39	L7	PE8	I/O	FT	-	USART4_TX	-
-	-	-	-	-	-	40	M8	PE9	I/O	FT	-	TIM2_CH1, TIM2_ETR, USART4_RX	-
-	-	-	-	-	-	41	L8	PE10	I/O	FT	-	TIM2_CH2, USART5_TX	-
-	-	-	-	-	-	42	M9	PE11	I/O	FT	-	TIM2_CH3, USART5_RX	-
-	-	-	-	-	-	43	L9	PE12	I/O	FT	-	TIM2_CH4, SPI1_NSS	-
-	-	-	-	-	-	44	M10	PE13	I/O	FT	-	SPI1_SCK	-
-	-	-	-	-	-	45	M11	PE14	I/O	FT	-	SPI1_MISO	-
-	-	-	-	-	-	46	M12	PE15	I/O	FT	-	SPI1_MOSI	-

Table 16. Alternate functions port A

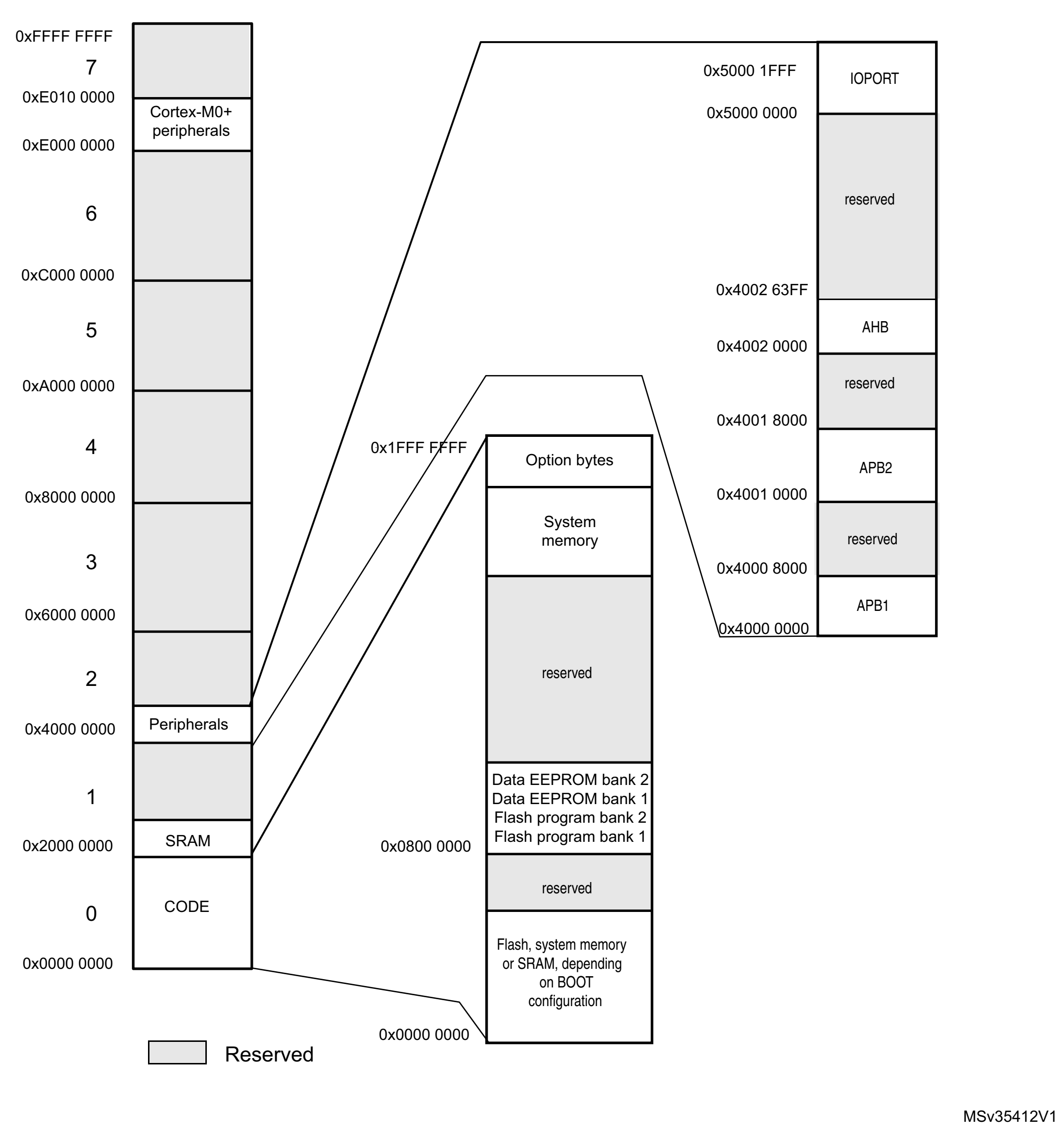
Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/SPI2/I2S2/USART1/2/ LPUART1/LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	**SPI1/SPI2/I2S2/I2C1/TIM2/21**	**SPI1/SPI2/I2S2/LPUART1/ USART5/LPTIM1 /TIM2/3/EVENTOUT/ SYS_AF**	**I2C1/ EVENTOUT**	**I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT**	**SPI2/I2S2/I2C2/USART1/ TIM2/21/22**	**I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/EVENTOUT**	**I2C3/LPUART1/COMP1/2/ TIM3**
Port A	PA0	-	-	TIM2_CH1		USART2_CTS	TIM2_ETR	USART4_TX	COMP1_OUT
	PA1	EVENTOUT		TIM2_CH2		USART2_RTS_DE	TIM21_ETR	USART4_RX	-
	PA2	TIM21_CH1		TIM2_CH3		USART2_TX	-	LPUART1_TX	COMP2_OUT
	PA3	TIM21_CH2		TIM2_CH4		USART2_RX	-	LPUART1_RX	-
	PA4	SPI1_NSS	-	-		USART2_CK	TIM22_ETR	-	-
	PA5	SPI1_SCK	-	TIM2_ETR			TIM2_CH1	-	-
	PA6	SPI1_MISO		TIM3_CH1		LPUART1_CTS	TIM22_CH1	EVENTOUT	COMP1_OUT
	PA7	SPI1_MOSI		TIM3_CH2		-	TIM22_CH2	EVENTOUT	COMP2_OUT
	PA8	MCO			EVENTOUT	USART1_CK	-	-	I2C3_SCL
	PA9	MCO		-		USART1_TX	-	I2C1_SCL	I2C3_SMBA
	PA10	-		-		USART1_RX	-	I2C1_SDA	-
	PA11	SPI1_MISO	-	EVENTOUT		USART1_CTS	-	-	COMP1_OUT
	PA12	SPI1_MOSI	-	EVENTOUT		USART1_RTS_DE	-	-	COMP2_OUT
	PA13	SWDIO	-		-	-	-	LPUART1_RX	-
	PA14	SWCLK	-	-	-	USART2_TX	-	LPUART1_TX	-
	PA15	SPI1_NSS		TIM2_ETR	EVENTOUT	USART2_RX	TIM2_CH1	USART4_RTS_DE	-

Table 21. Alternate functions port H

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/SPI2/ I2S2/USART1/2/ LPUART1/ LPTIM1/ TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2 /I2C1/TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/ LPTIM1/TIM2/3/ EVENTOUT/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/ LPUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2/I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/ EVENTOUT	I2C3/ LPUART1/ COMP1/2/ TIM3
Port H	PH0		-	-	-	-	-	-	-
	PH1	-	-	-	-	-	-	-	-
	PH9	-	-	-	-	-	-	-	-
	PH10	-	-	-	-	-	-	-	-

5 Memory mapping

Figure 11. Memory map



1. Refer to the STM32L071xx reference manual for details on the Flash memory organization for each memory size.

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 22: Voltage characteristics*, *Table 23: Current characteristics*, and *Table 24: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 22. Voltage characteristics

Symbol	Definition	Min	Max	Unit
$V_{DD}–V_{SS}$	External main supply voltage (including V_{DDA}, V_{DDIO2} V_{DD})[1]	–0.3	4.0	V
V_{IN}[2]	Input voltage on FT and FTf pins	$V_{SS} - 0.3$	V_{DD}+4.0	
	Input voltage on TC pins	$V_{SS} - 0.3$	4.0	
	Input voltage on BOOT0	V_{SS}	$V_{DD} + 4.0$	
	Input voltage on any other pin	$V_{SS} - 0.3$	4.0	
$\|\Delta V_{DD}\|$	Variations between different V_{DDx} power pins	-	50	mV
$\|V_{DDA}-V_{DDx}\|$	Variations between any V_{DDx} and V_{DDA} power pins[3]	-	300	
$\|\Delta V_{SS}\|$	Variations between all different ground pins including V_{REF-} pin	-	50	
V_{REF+} –V_{DDA}	Allowed voltage difference for $V_{REF+} > V_{DDA}$	-	0.4	V
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.11*		

1. All main power (V_{DD},, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 23* for maximum allowed injected current values.
3. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and device operation. V_{DDIO2} is independent from V_{DD} and V_{DDA}: its value does not need to respect this rule.

Table 29. Current consumption in Run mode, code with data processing running from Flash memory

Symbol	Parameter	Condition		f_{HCLK} (MHz)	Typ	Max(1)	Unit
I_{DD} (Run from Flash memory)	Supply current in Run mode code executed from Flash memory	f_{HSE} = f_{HCLK} up to 16MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range3, Vcore=1.2 V VOS[1:0]=11	1	190	250	µA
				2	345	380	
				4	650	670	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	0,8	0,86	mA
				8	1,55	1,7	
				16	2,95	3,1	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	1,9	2,1	
				16	3,55	3,8	
				32	6,65	7,2	
		MSI clock source	Range3, Vcore=1.2 V VOS[1:0]=11	0,065	39	130	µA
				0,524	115	210	
				4,2	700	770	
		HSI clock source (16MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	2,9	3,2	mA
			Range1, Vcore=1.8 V VOS[1:0]=01	32	7,15	7,4	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 30. Current consumption in Run mode vs code type, code with data processing running from Flash memory

Symbol	Parameter	Conditions			f_{HCLK}	Typ	Unit
I_{DD} (Run from Flash memory)	Supply current in Run mode, code executed from Flash memory	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL on)(1)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	650	µA
				CoreMark		655	
				Fibonacci		485	
				while(1)		385	
				while(1), 1WS, prefetch off		375	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	Dhrystone	32 MHz	6,65	mA
				CoreMark		6,9	
				Fibonacci		6,75	
				while(1)		5,8	
				while(1), prefetch off		5,5	

1. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

6.3.6 External clock source characteristics

High-speed external user clock generated from an external source

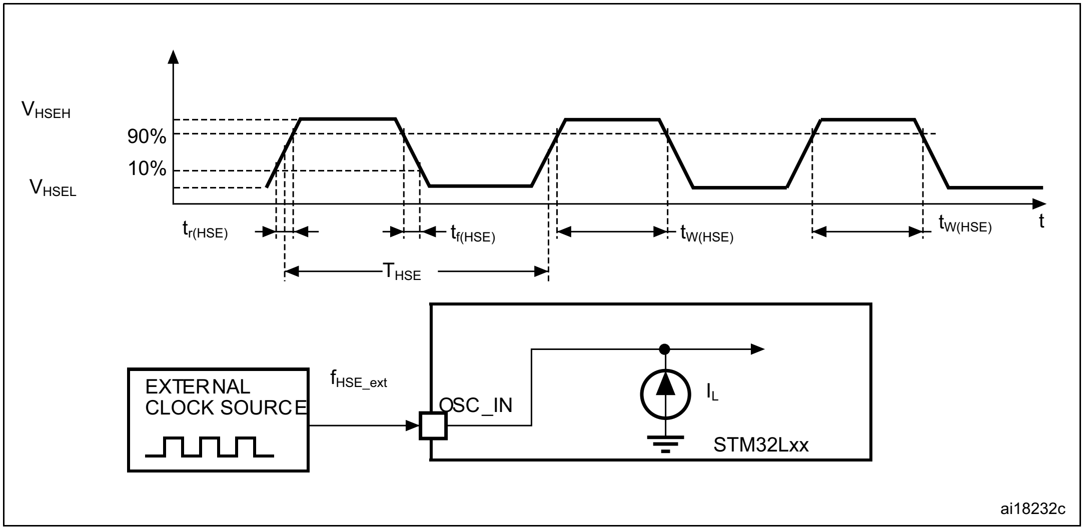
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.The external clock signal has to respect the I/O characteristics in *Section 6.3.12*. However, the recommended clock input waveform is shown in *Figure 21*.

Table 42. High-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	CSS is on or PLL is used	1	8	32	MHz
		CSS is off, PLL not used	0	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time		12	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance		-	2.6	-	pF
$DuCy_{(HSE)}$	Duty cycle		45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Figure 21. High-speed external clock source AC timing diagram



Low-speed external user clock generated from an external source

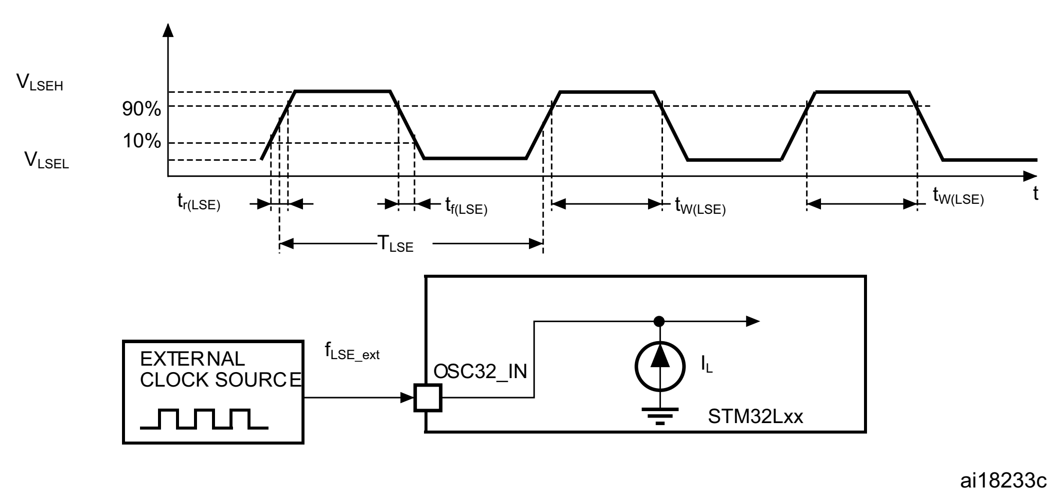
The characteristics given in the following table result from tests performed using a low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 25*.

Table 43. Low-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	-	1	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{w(LSE)}$	OSC32_IN high or low time		465	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time		-	-	10	
$C_{IN(LSE)}$	OSC32_IN input capacitance	-	-	0.6	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design, not tested in production

Figure 22. Low-speed external clock source AC timing diagram



Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 28* and *Table 60*, respectively.

Unless otherwise specified, the parameters given in *Table 60* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 25*.

Table 60. I/O AC characteristics(1)

OSPEEDRx[1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(2)	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	100	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	320	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	0.6	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	65	
10	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	13	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	28	
11	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	35	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	10	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	6	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	17	
Fm+ configuration(4)	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.5 V to 3.6 V	-	1	MHz
	$t_{f(IO)out}$	Output fall time		-	10	ns
	$t_{r(IO)out}$	Output rise time		-	30	
	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 1.65 V to 3.6 V	-	350	KHz
	$t_{f(IO)out}$	Output fall time		-	15	ns
	$t_{r(IO)out}$	Output rise time		-	60	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. The maximum frequency is defined in *Figure 28*.
4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.

I2S characteristics

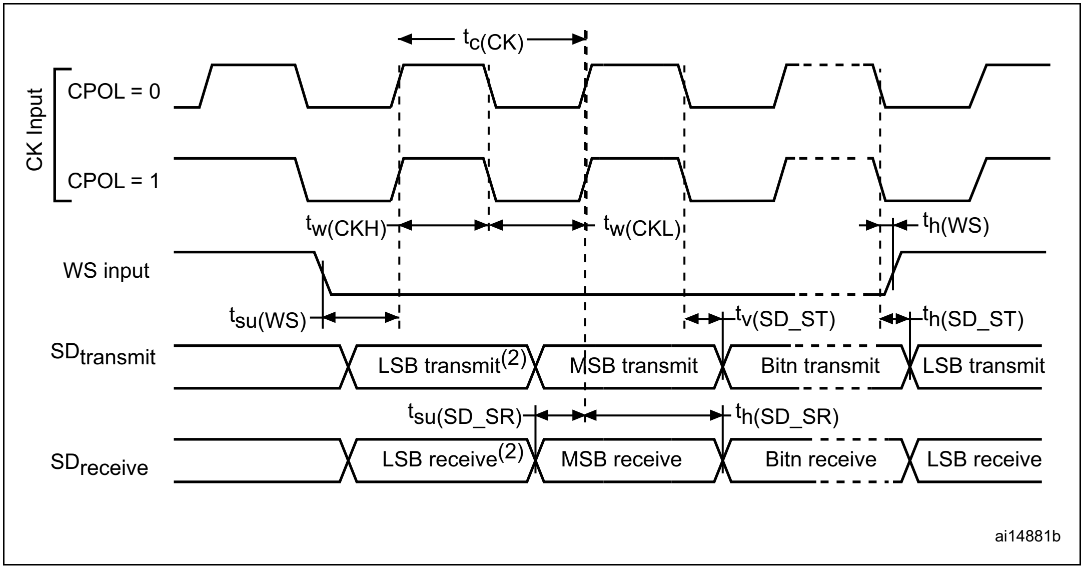
Table 75. I2S characteristics[1]

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCK}	I2S Main clock output	-	256 x 8K	256xFs [2]	MHz
f_{CK}	I2S clock frequency	Master data: 32 bits	-	64xFs	MHz
		Slave data: 32 bits	-	64xFs	
D_{CK}	I2S clock frequency duty cycle	Slave receiver	30	70	%
$t_{v(WS)}$	WS valid time	Master mode	-	15	ns
$t_{h(WS)}$	WS hold time	Master mode	11	-	
$t_{su(WS)}$	WS setup time	Slave mode	6	-	
$t_{h(WS)}$	WS hold time	Slave mode	2	-	
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	0	-	
$t_{su(SD\_SR)}$		Slave receiver	6.5	-	
$t_{h(SD\_MR)}$	Data input hold time	Master receiver	18	-	
$t_{h(SD\_SR)}$		Slave receiver	15.5	-	
$t_{v(SD\_ST)}$	Data output valid time	Slave transmitter (after enable edge)	-	77	
$t_{v(SD\_MT)}$		Master transmitter (after enable edge)	-	8	
$t_{h(SD\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	18	-	
$t_{h(SD\_MT)}$		Master transmitter (after enable edge)	1.5	-	

1. Guaranteed by characterization results.
2. 256xFs maximum value is equal to the maximum clock frequency.

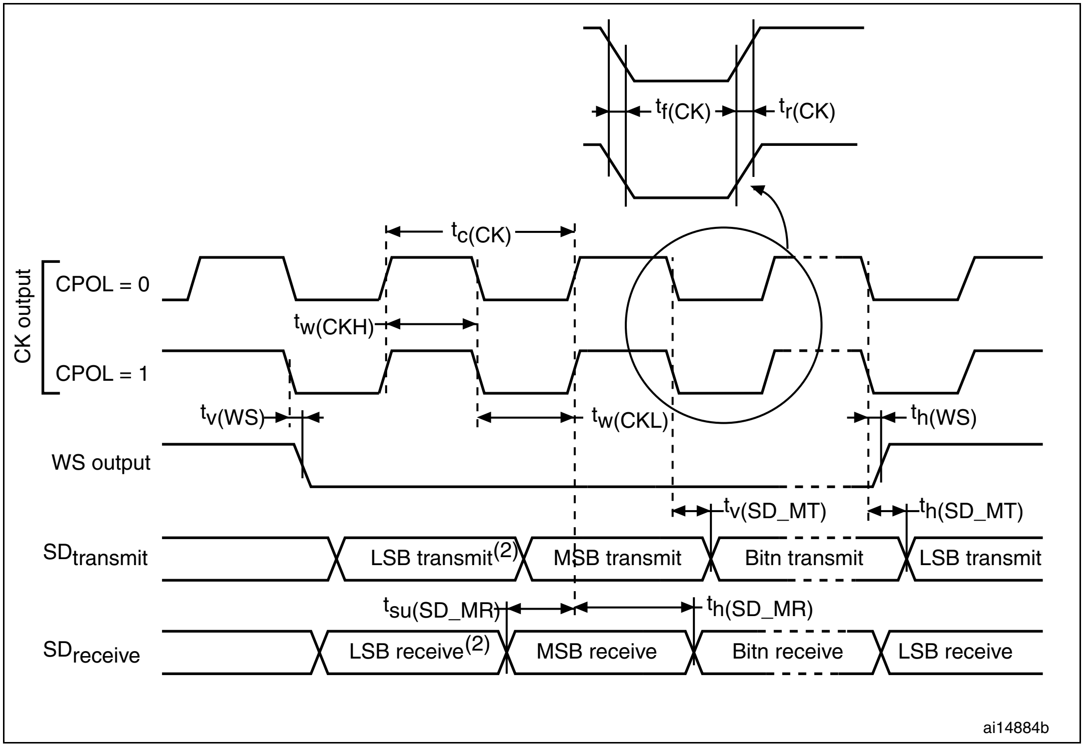
*Note: Refer to the I2S section of the product reference manual for more details about the sampling frequency (Fs), f_{MCK}, f_{CK} and D_{CK} values. These values reflect only the digital peripheral behavior, source clock precision might slightly change them. DCK depends mainly on the ODD bit value, digital contribution leads to a min of (I2SDIV/(2*I2SDIV+ODD) and a max of (I2SDIV+ODD)/(2*I2SDIV+ODD). Fs max is supported for each mode/condition.*

Figure 37. I^2S slave timing diagram (Philips protocol)(1)



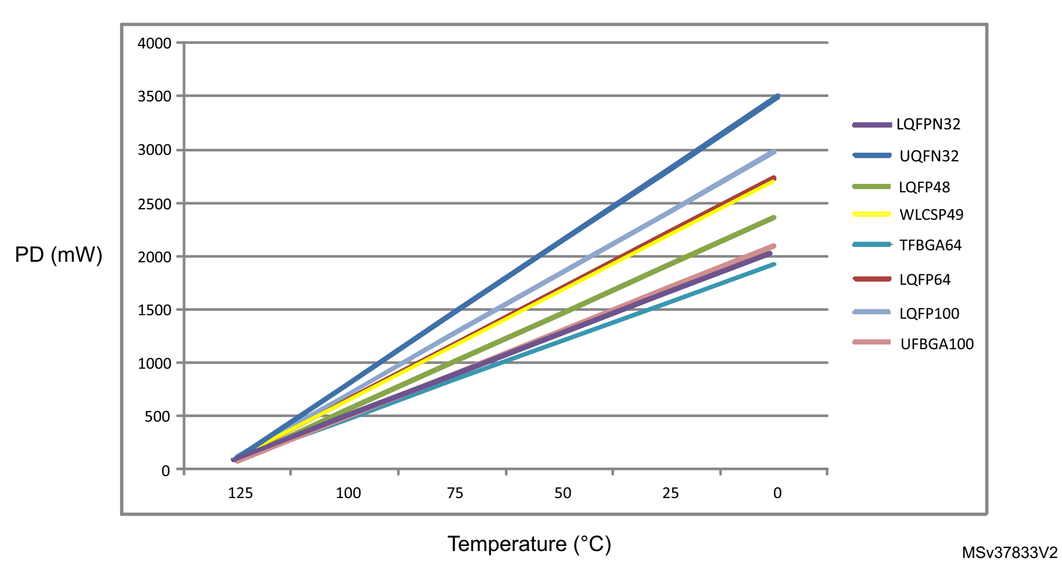
1. Measurement points are done at CMOS levels: 0.3 × V_{DD} and 0.7 × V_{DD}.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 38. I^2S master timing diagram (Philips protocol)(1)



1. Guaranteed by characterization results.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 62. Thermal resistance



7.9.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

9 Revision history

Table 89. Document revision history

Date	Revision	Changes
02-Sep-2015	1	Initial release
26-Oct-2015	2	Changed confidentiality level to public. Updated datasheet status to “production data”. Modified ultra-low-power platform features on cover page. In *Table 15: STM32L071xxx pin definition*: – changed pin name to VDDIO2 for the following pins: UFQFPN32 pin 24, LQFP48 pin 36, LQFP64 pin 48, UFBGA64 pin E5, WLCSP49 pin A1, LQFP100 pin 75 and UFBGA100 pin G11. – Added note related to UFQFPN32. In *Section 6: Electrical characteristics*, updated notes related to values guaranteed by characterization. Updated $\|\Delta V_{SS}\|$ definition to include V_{REF-} in *Table 22: Voltage characteristics*. Updated f_{TRIG} and V_{AIN} maximum value, added V_{REF+} and V_{REF-} in *Table 62: ADC characteristics*. Added *Section : Device marking for LQFP100*. Updated *Figure 42: UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline* and *Table 76: LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data*. Added *Section : Device marking for LQFP100*, *Section : Device marking for LQFP64*, *Section : Device marking for TFBGA64* and *Section : Device marking for WLCSP49*. Updated *Figure 55: LQFP48 marking example (package top view)*.